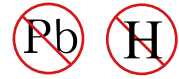




SEMICONDUCTOR

DATA SHEET

GS1A-A THRU GS1M-A



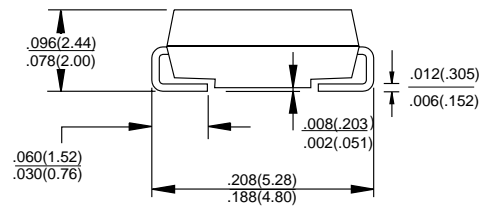
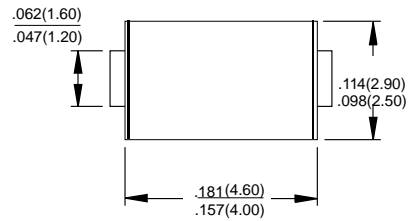
SURFACE MOUNT RECTIFIER

VOLTAGE- 50 to 1000 Volts CURRENT - 1.0 Amperes

FEATURES

- For surface mounted applications
- Low profile package
- Built-in strain relief
- Easy pick and place
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Low Forward Drop
- Glass passivated diode Junction
- High temperature soldering : 260°C / 10 seconds at terminals
- Pb free product at available: 99% Sn above meet RoHS environment substance directive request
- AEC-Q101 qualified

SMA/DO-214AC Unit: inch(mm)



MECHANICAL DATA

- Case : JEDEC DO-214AC molded plastic
- Base P/N - RoHS compliant, commercial grade
- Base P/N-A - RoHS compliant, AEC-Q101 qualified
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Indicated by cathode band
- Standard packaging: 12mm tape (EIA-481)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25° C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

	SYMBOLS	GS1A	GS1B	GS1D	GS1G	GS1J	GS1K	GS1M	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current, at TL=75°C	I(AV)	1.0							A
Peak Forward Surge Current 8.3ms single half sine-wave super imposed on rated load (JEDEC method)	IFSM	30.0							A
Maximum Instantaneous Forward Voltage at 1.0A	VF	1.1							V
Maximum DC Reverse Current TA=25°C at Rated DC Blocking Voltage TA=125°C	IR	5.0							μA
		100							μA
Maximum Reverse Recovery Time(Note 1) TJ=25°C	TRR	2.5							μs
Typical Junction Capacitance (Note 2)	CJ	2.5							Pf
Maximum Thermal Resistance(Note 3)	RθJA	15.0							° C / W
Operating and Storage Temperature Range	TJ , TSTG	-55 to +150							° C

NOTES:

1. Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, I rr=0.25A
2. Measured at 1 MHz and applied Vr = 4.0 volts.
3. 8.0 mm² (.013mm thick) land areas.

RATING AND CHARACTERISTIC CURVES

GS1A-A THRU GS1M-A

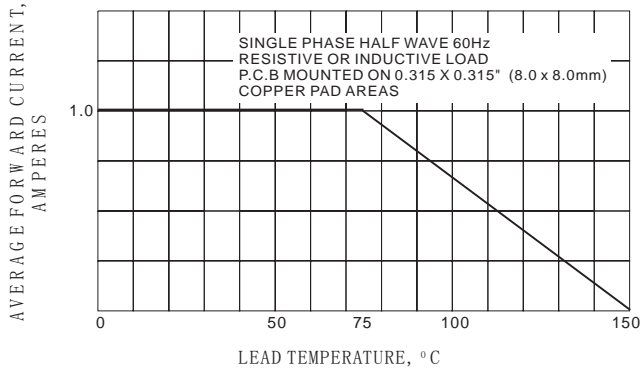


Fig. 1-FORWARD CURRENT DERATING CURVE

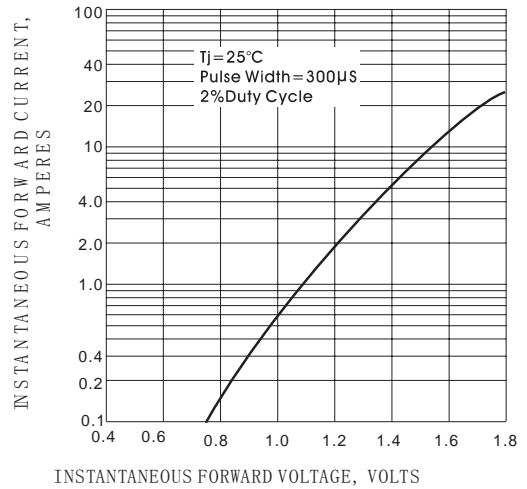


Fig. 2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

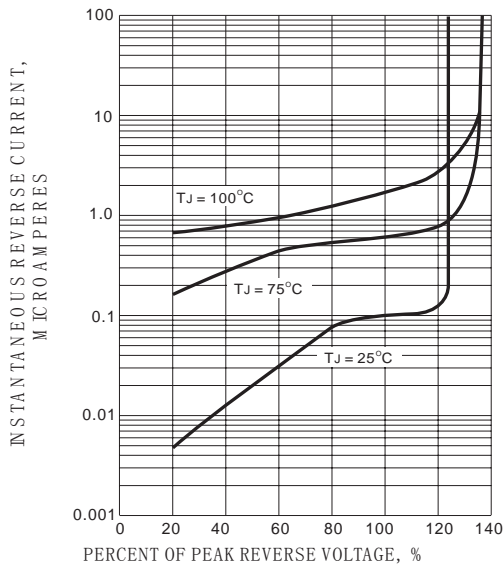


Fig. 3-TYPICAL REVERSE CHARACTERISTICS

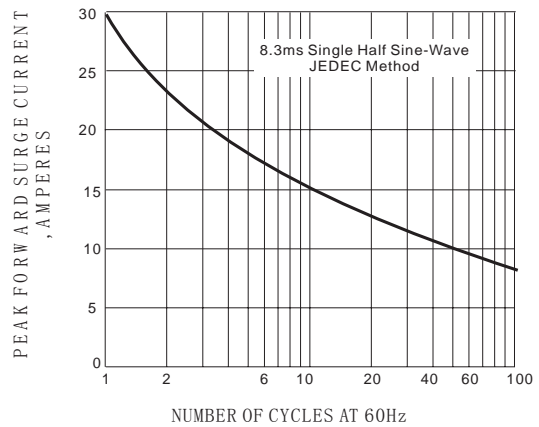


Fig. 4-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

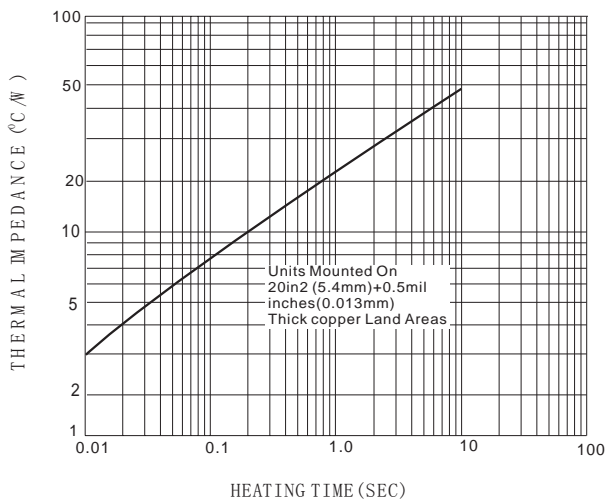


Fig. 5-TRANSIENT THERMAL IMPEDANCE

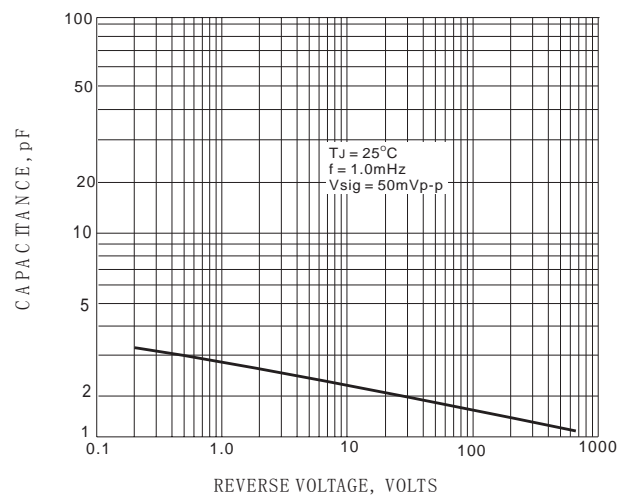


Fig. 6-TYPICAL JUNCTION CAPACITANCE